MC14572UB

Hex Gate

The MC14572UB hex functional gate is constructed with MOS P−channel and N−channel enhancement mode devices in a single monolithic structure. These complementary MOS logic gates find primary use where low power dissipation and/or high noise immunity is desired. The chip contains four inverters, one NOR gate and one NAND gate.

Features

- Diode Protection on All Inputs
- Single Supply Operation
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- NOR Input Pin Adjacent to V_{SS} Pin to Simplify Use As An Inverter
- NAND Input Pin Adjacent to V_{DD} Pin to Simplify Use As An Inverter
- NOR Output Pin Adjacent to Inverter Input Pin For OR Application
- NAND Output Pin Adjacent to Inverter Input Pin For AND Application
- Capable of Driving Two Low−Power TTL Loads or One Low−Power Schottky TTL Load over the Rated Temperature Range
- These Devices are Pb−Free and are RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Parameter	Symbol	Value	Unit
DC Supply Voltage Range	V_{DD}	−0.5 to +18.0	V
Input or Output Voltage Range (DC or Transient)	V_{in}, V_{out}	−0.5 to V_{DD} + 0.5	V
Input or Output Current (DC or Transient) per Pin	I_{in}, I_{out}	±10	mA
Power Dissipation, per Package (Note 1)	P_D	500	mW
Ambient Temperature Range	T_A	−55 to +125	°C
Storage Temperature Range	T_{stg}	−65 to +150	°C
Lead Temperature (8−Second Soldering)	T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Temperature Derating: Plastic “P and D/DW” Packages: − 7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high−impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

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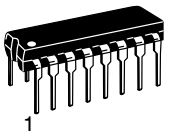
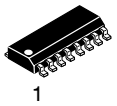
MARKING DIAGRAMS



PDIP−16
P SUFFIX
CASE 648



SOIC−16
D SUFFIX
CASE 751B

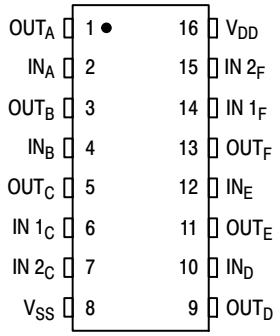
A	= Assembly Location
WL	= Wafer Lot
YY	= Year
WW	= Work Week
G	= Pb−Free Package

ORDERING INFORMATION

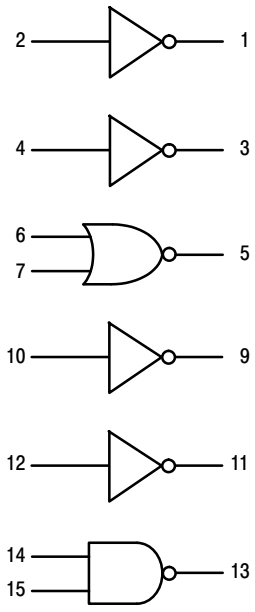
Device	Package	Shipping†
MC14572UBCPG	PDIP−16 (Pb−Free)	25 Units / Rail
MC14572UBDG	SOIC−16 (Pb−Free)	48 Units / Rail
MC14572UBDR2G	SOIC−16 (Pb−Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PIN ASSIGNMENT

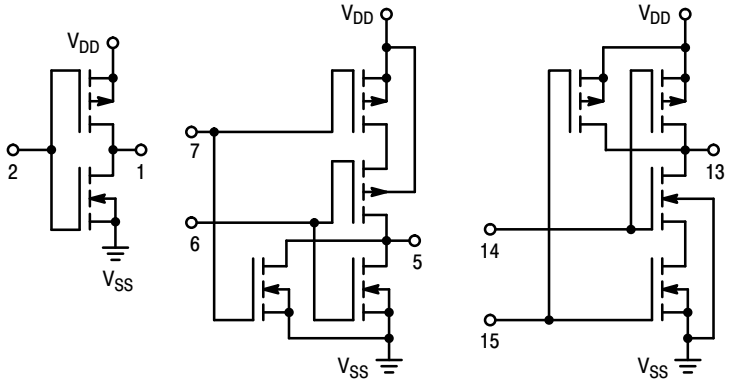


LOGIC DIAGRAM



V_{DD} = PIN 16
V_{SS} = PIN 8

CIRCUIT SCHEMATIC



ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	– 55°C Min	– 55°C Max	25°C Min	25°C Typ (Note 2)	25°C Max	125°C Min	125°C Max	Unit
Output Voltage "0" Level V_{in} = V_{DD} or 0	V_{OL}	5.0 10 15	– – –	0.05 0.05 0.05	– – –	0 0 0	0.05 0.05 0.05	– – –	0.05 0.05 0.05	Vdc
V_{in} = 0 or V_{DD} "1" Level	V_{OH}	5.0 10 15	4.95 9.95 14.95	– – –	4.95 9.95 14.95	5.0 10 15	– – –	4.95 9.95 14.95	– – –	Vdc
Input Voltage "0" Level (V_O = 4.5 or 0.5 Vdc) (V_O = 9.0 or 1.0 Vdc) (V_O = 13.5 or 1.5 Vdc)	V_{IL}	5.0 10 15	– – –	1.0 2.0 2.5	– – –	2.25 4.50 6.75	1.0 2.0 2.5	– – –	1.0 2.0 2.5	Vdc
"1" Level (V_O = 0.5 or 4.5 Vdc) (V_O = 1.0 or 9.0 Vdc) (V_O = 1.5 or 13.5 Vdc)	V_{IH}	5.0 10 15	4.0 8.0 12.5	– – –	4.0 8.0 12.5	2.75 5.50 8.25	– – –	4.0 8.0 12.5	– – –	Vdc
Output Drive Current (V_{OH} = 2.5 Vdc) Source (V_{OH} = 4.6 Vdc) (V_{OH} = 9.5 Vdc) (V_{OH} = 13.5 Vdc)	I_{OH}	5.0 5.0 10 15	– 1.2 – 0.25 – 0.62 – 1.8	– – – –	– 1.0 – 0.2 – 0.5 – 1.5	– 1.7 – 0.36 – 0.9 – 3.5	– – – –	– 0.7 – 0.14 – 0.35 – 1.1	– – – –	mAdc
(V_{OL} = 0.4 Vdc) Sink (V_{OL} = 0.5 Vdc) (V_{OL} = 1.5 Vdc)	I_{OL}	5.0 10 15	0.64 1.6 4.2	– – –	0.51 1.3 3.4	0.88 2.25 8.8	– – –	0.36 0.9 2.4	– – –	mAdc
Input Current	I_{in}	15	–	±0.1	–	±0.00001	±0.1	–	±1.0	μAdc
Input Capacitance (V_{in} = 0)	C_{in}	–	–	–	–	5.0	7.5	–	–	pF
Quiescent Current (Per Package)	I_{DD}	5.0 10 15	– – –	0.25 0.5 1.0	– – –	0.0005 0.0010 0.0015	0.25 0.5 1.0	– – –	7.5 15 30	μAdc
Total Supply Current (Notes 3, 4) (Dynamic plus Quiescent, Per Package) (C_L = 50 pF on all outputs, all buffers switching)	I_T	5.0 10 15	I_T = (1.89 μA/kHz) f + I_{DD} I_T = (3.80 μA/kHz) f + I_{DD} I_T = (5.68 μA/kHz) f + I_{DD}							μAdc

2. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
3. The formulas given are for the typical characteristics only at 25°C.
4. To calculate total supply current at loads other than 50 pF: $I_T(C_L) = I_T(50\ pF) + (C_L - 50)$ Vfk where: I_T is in μA (per package), C_L in pF, V = ($V_{DD} - V_{SS}$) in volts, f in kHz is input frequency, and k = 0.006.

SWITCHING CHARACTERISTICS (Type 5) (C_L = 50 pF, T_A = 25°C)

Characteristic	Symbol	V_{DD}	Min	Typ (Note 6)	Max	Unit
Output Rise Time	t_{TLH}					ns
t_{TLH} = (3.0 ns/pF) C_L + 30 ns		5.0	–	180	360	
t_{TLH} = (1.5 ns/pF) C_L + 15 ns		10	–	90	180	
t_{TLH} = (1.1 ns/pF) C_L + 10 ns		15	–	65	130	
Output Fall Time	t_{THL}					ns
t_{THL} = (1.5 ns/pF) C_L + 25 ns		5.0	–	100	200	
t_{THL} = (0.75 ns/pF) C_L + 12.5 ns		10	–	50	100	
t_{THL} = (0.55 ns/pF) C_L + 9.5 ns		15	–	40	80	
Propagation Delay Time	t_{PLH}, t_{PHL}					ns
t_{PLH}, t_{PHL} = (1.7 ns/pF) C_L + 5 ns		5.0	–	90	180	
t_{PLH}, t_{PHL} = (0.66 ns/pF) C_L + 17 ns		10	–	50	100	
t_{PLH}, t_{PHL} = (0.5 ns/pF) C_L + 15 ns		15	–	40	80	

5. The formulas given are for the typical characteristics only at 25°C.
6. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.

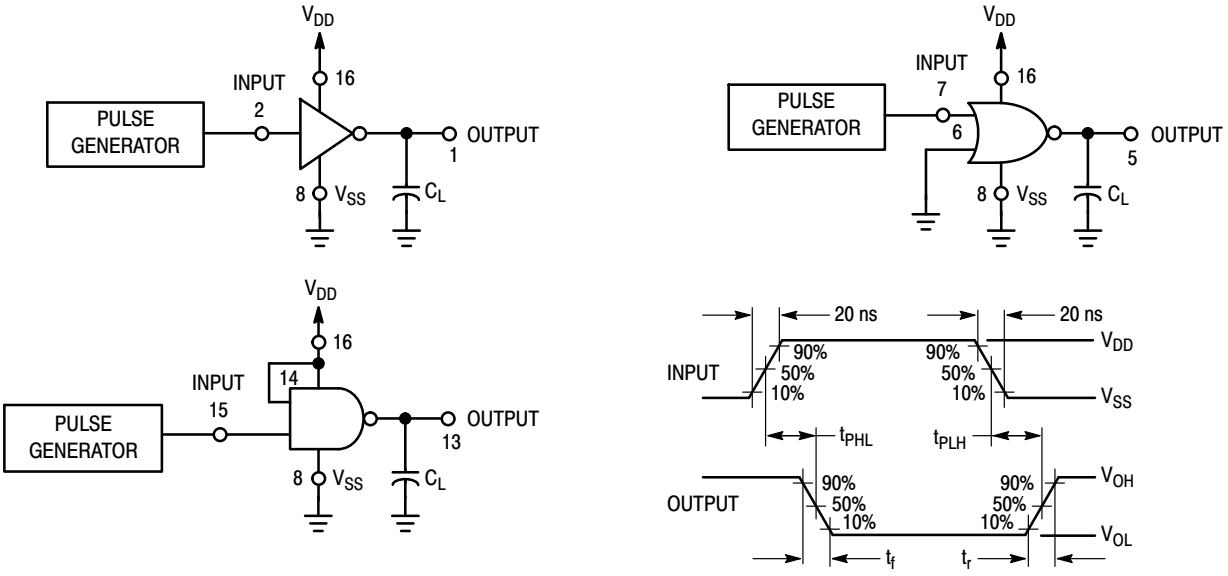
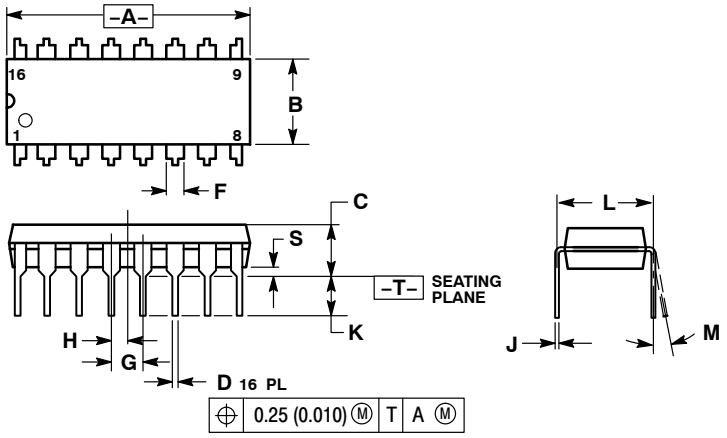


Figure 1. Switching Time Test Circuits and Waveforms

PACKAGE DIMENSIONS

PDIP−16
CASE 648−08
ISSUE T

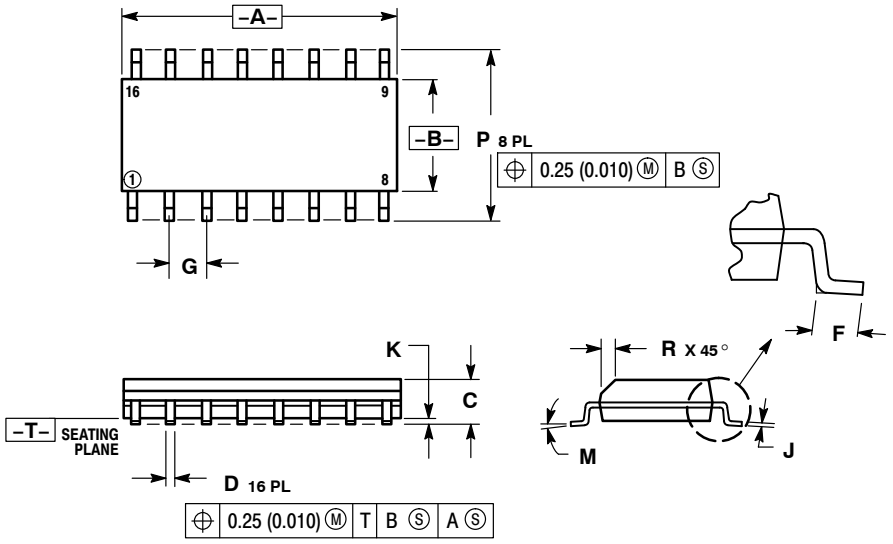


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.740	0.770	18.80	19.55
B	0.250	0.270	6.35	6.85
C	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100 BSC		2.54 BSC	
H	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0 °	10 °	0 °	10 °
S	0.020	0.040	0.51	1.01

PACKAGE DIMENSIONS

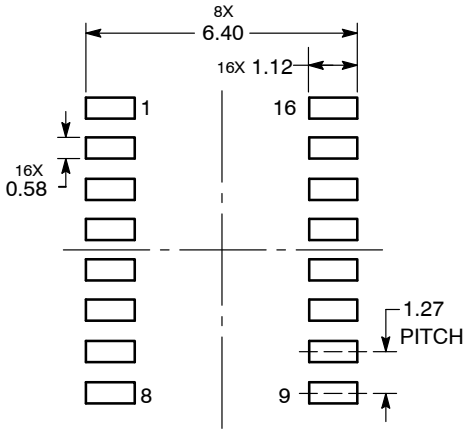
SOIC−16
CASE 751B−05
ISSUE K



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

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